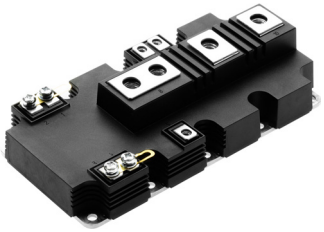
Half Bridge IGBT Module

multicomp PRO

RoHS Compliant



Features

- Trench Gate, Generation 5, TMOS IGBT
- Cu Base with Al_2O_3 Substrates
- High Thermal Cycling Capability
- 10µs Short Circuit Withstand
- High Current Density

Key Parameters

V_{CES}	: 1700 V
$V_{CE(sat)}$ * (typ)	: 1.85
I_C (max)	: 650 A
$I_{C(PK)}$ (max)	: 1300 A

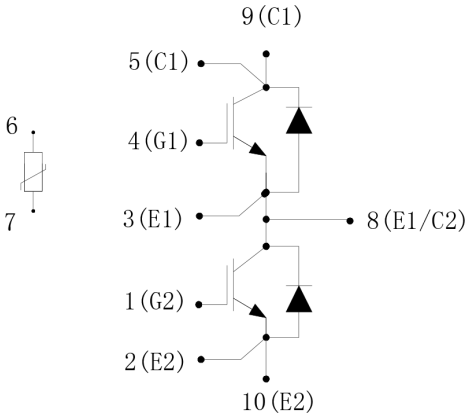
* Measured at the auxiliary terminals

Applications

- Motor Drives
- High Power Converters
- Renewable Energy Power Conversion
- High Reliability Inverters

The MP005810 is a half bridge 1700V, trench gate, insulated gate bipolar transistor (IGBT) module with enhanced field stop and implantation technology. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.



Circuit configuration

Absolute Maximum Ratings

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V, T_C = 25°C	1700	V
V_{GES}	Gate-emitter voltage	T_C = 25°C	±20	
I_C	Continuous collector current	T_C = 105°C	650	A
$I_{C(PK)}$	Peak collector current	t_P = 1ms	1300	
P_{max}	Max. transistor power dissipation	T_C = 25°C, T_{vj} = 150°C	4.16	kW
I^2t	Diode I^2t value	V_R = 0, tp = 10ms, Tvj = 150°C	64	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4000	V

Thermal and Mechanical Ratings

Internal insulation material : Al_2O_3
Baseplate material : Cu
Creepage distance – Terminal to heatsink : 33mm
Creepage distance – Terminal to terminal : 33mm
Clearance – Terminal to heatsink : 19mm
Clearance – Terminal to terminal : 19mm
CTI (Comparative Tracking Index) : >400

Symbol	Parameter	Test Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance– IGBT	Continuous dissipation - junction to case	-	30	°C/kW
$R_{th(j-c)}$	Thermal resistance – diode			54	
$R_{th(c-h)}$	Thermal resistance – case to heatsink (IGBT)	Mounting torque 5Nm (with mounting grease 1W/m °C)	-	19.5	
$R_{th(c-h)}$	Thermal resistance – case to heatsink (Diode)			35	
T_j	Junction temperature	IGBT	-40	150	°C
		Diode			
F_{stg}	Storage temperature range	-			
	Screw torque	Mounting – M5	3	6	Nm
		Electrical connections – M8	8	10	

Electrical Characteristics

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = V_{CES}			1	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125°C			20	
		V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150°C			30	
I_{GES}	Gate leakage current	V_{GE} = ± 20V, V_{CE} = 0V			0.5	µA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 40mA, V_{GE} = V_{CE}	5.2	5.8	6.4	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 650A		1.85	2.25	
		V_{GE} = 15V, I_C = 650A, T_j = 125°C		2.2	2.6	
		V_{GE} = 15V, I_C = 650A, T_j = 150°C		2.3	2.7	
I_F	Diode forward current	DC		650		A
I_{FM}	Diode maximum forward current	t_p = 1ms		1300		
V_F	Diode forward voltage	I_F = 650A		1.8	2.2	V
		I_F = 650A, T_j = 125°C		1.9	2.3	
		I_F = 650A, T_j = 150°C				
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 100kHz		83		nF
Q_g	Gate charge	±15V		7.7		µC
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 100kHz		1		nF
L_M	Module inductance			18		nH
R_{INT}	Internal transistor resistance			0.3		mΩ
SC_{Data}	Short circuit current, I_{SC}	T_j = 150°C, V_{CC} = 1000V t_p ≤ 10µs, V_{GE} ≤ 15V $V_{CE\ (max)}$ = V_{CES} – L* x dI/dt IEC 60747-9		3300		A

Note:
* L is the circuit inductance + L_M

NTC-Thermistor Data

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Units
R_{25}	Rated Resistance	T_C = 25°C		5		kΩ
ΔR/R	Deviation of R100	T_C = 100°C, R_{100} = 493Ω	-5		5	%
P_{25}	Power Dissipation	T_C = 25°C			20	m/W
$B_{25/50}$	B-value	$R_2 = R_{25}\exp[B_{25/50}(1/T2 - 1/(298.15K))]$		3375		K
$B_{25/80}$		$R_2 = R_{25}\exp[B_{25/80}(1/T2 - 1/(298.15K))]$		3411		
$B_{25/100}$		$R_2 = R_{25}\exp[B_{25/100}(1/T2 - 1/(298.15K))]$		3433		

Electrical Characteristics

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions		Min.	Typ	Max.	Units
$t_{d(off)}$	Turn-off delay time	I_C = 650A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 2.7Ω $R_{G(ON)}$ = 1.8Ω L_S ~ 70nH	dv/dt = 4500V/µs		1055		ns
t_f	Fall time				360		
E_{OFF}	Turn-off energy loss				155		mJ
$t_{d(on)}$	Turn-on delay time		di/dt = 4200A/µs		495		ns
t_r	Rise time				170		
E_{ON}	Turn-on energy loss				165		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 650A V_{CE} = 900V di/dt = 4200A/µs			155		µC
I_{rr}	Diode reverse recovery current				610		A
E_{rec}	Diode reverse recovery energy				100		mJ

T_{case} = 125°C unless stated otherwise.

Symbol	Parameter	Test Conditions		Min.	Typ	Max.	Units
$t_{d(off)}$	Turn-off delay time	I_C = 650A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 2.7Ω $R_{G(ON)}$ = 1.8Ω L_S ~ 70nH	dv/dt = 4500V/µs		1145		ns
t_f	Fall time				450		
E_{OFF}	Turn-off energy loss				200		mJ
$t_{d(on)}$	Turn-on delay time		di/dt = 4200A/µs		485		ns
t_r	Rise time				170		
E_{ON}	Turn-on energy loss				195		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 650A V_{CE} = 900V di/dt = 4200A/µs			250		µC
I_{rr}	Diode reverse recovery current				700		A
E_{rec}	Diode reverse recovery energy				165		mJ

T_{case} = 150°C unless stated otherwise.

Symbol	Parameter	Test Conditions		Min.	Typ	Max.	Units
$t_{d(off)}$	Turn-off delay time	I_C = 650A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 2.7Ω $R_{G(ON)}$ = 1.8Ω L_S ~ 70nH	dv/dt = 4500V/µs		1170		ns
t_f	Fall time				550		
E_{OFF}	Turn-off energy loss				210		mJ
$t_{d(on)}$	Turn-on delay time		di/dt = 4200A/µs		480		ns
t_r	Rise time				160		
E_{ON}	Turn-on energy loss				210		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 650A V_{CE} = 900V di/dt = 4200A/µs			280		µC
I_{rr}	Diode reverse recovery current				780		A
E_{rec}	Diode reverse recovery energy				190		mJ

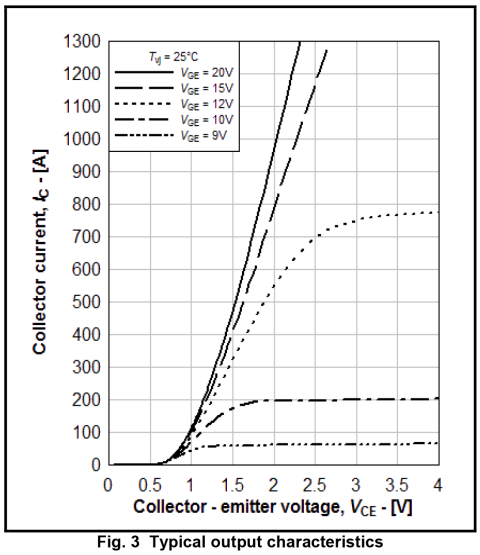


Fig. 3 Typical output characteristics

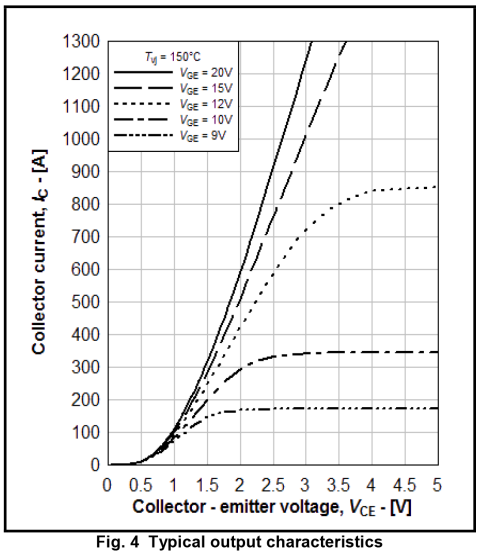


Fig. 4 Typical output characteristics

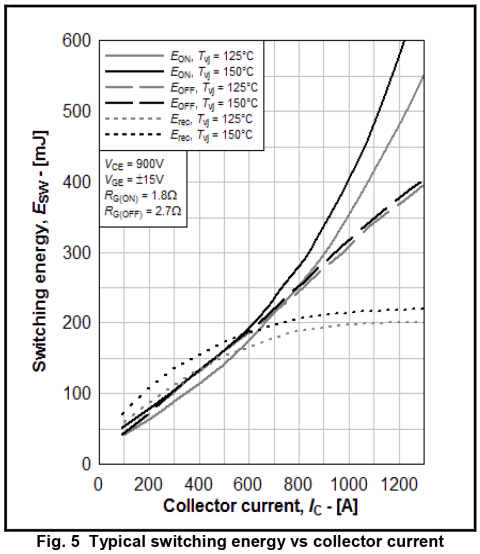


Fig. 5 Typical switching energy vs collector current

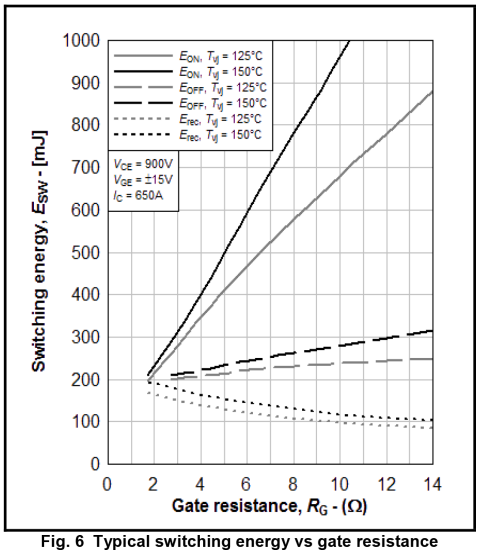


Fig. 6 Typical switching energy vs gate resistance

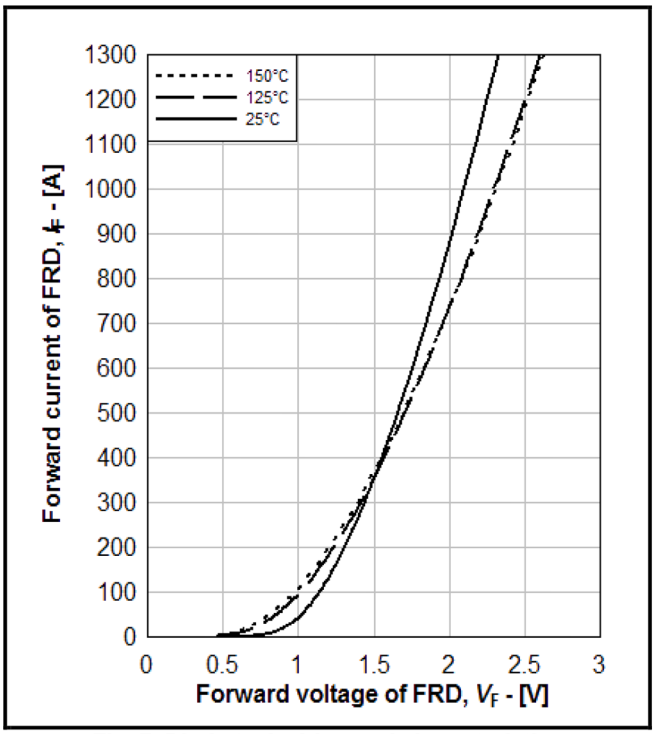


Fig. 7 Diode typical forward characteristics

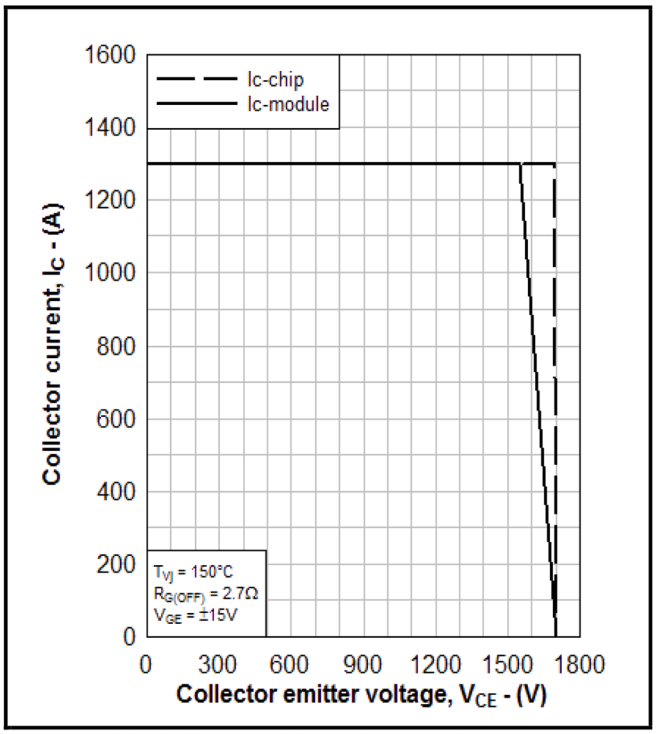


Fig. 8 Reverse bias safe operating area

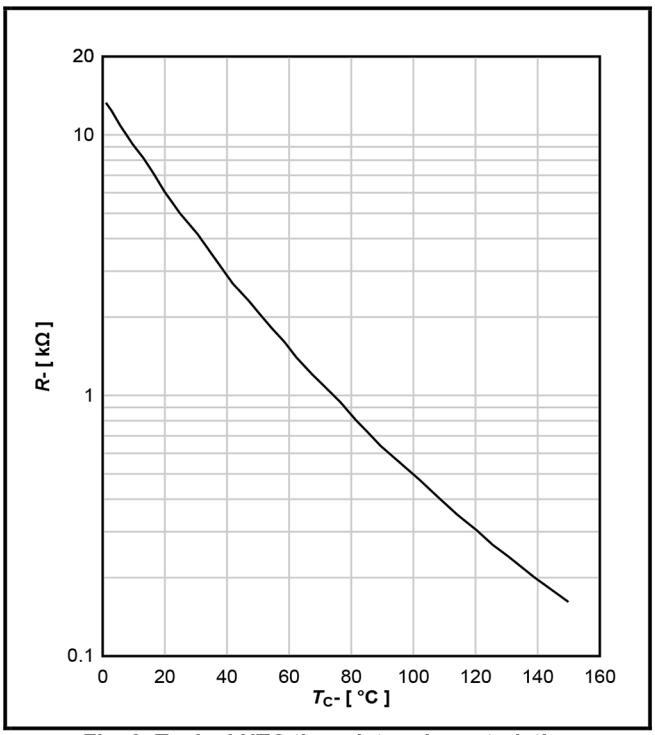


Fig. 9 Typical NTC thermistor characteristics

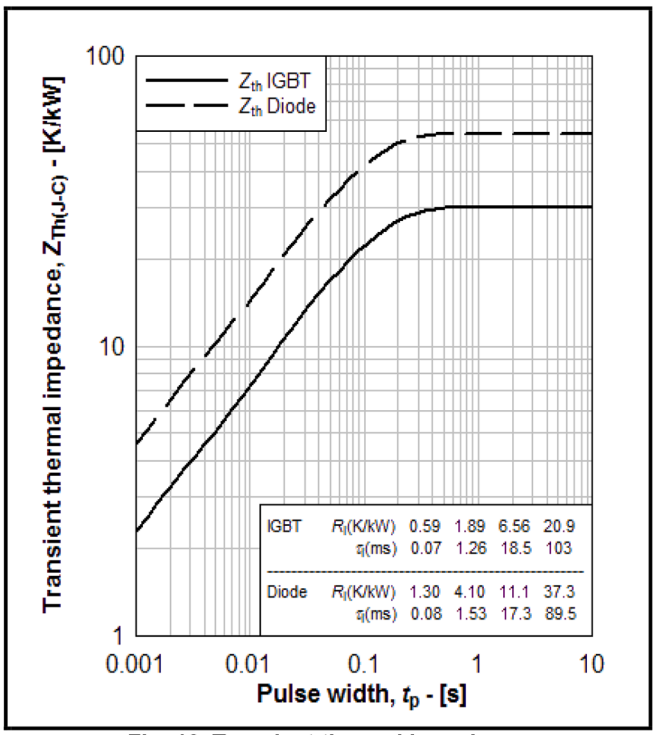
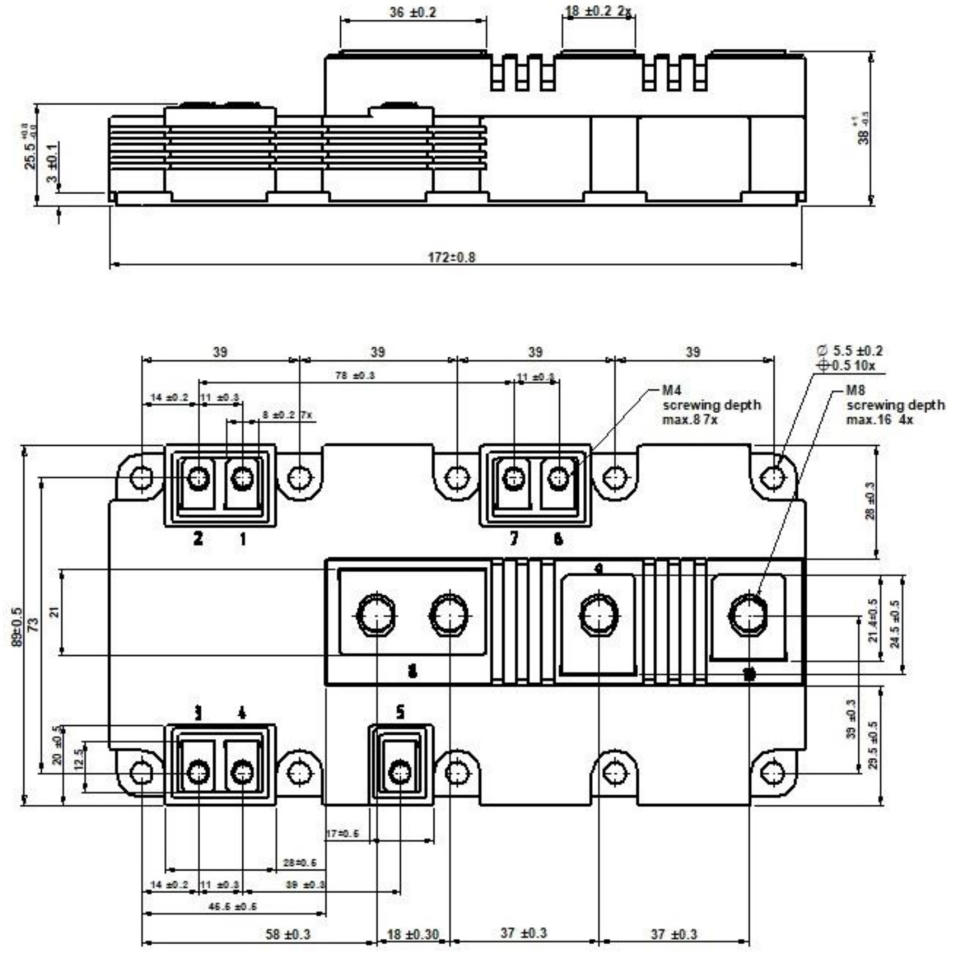


Fig. 10 Transient thermal impedance



Nominal Weight: 900g

Part Number Table

Description	Part Number
Half Bridge IGBT Module, 1700V, 650A, H2 Case Code	MPIM650H217TG5